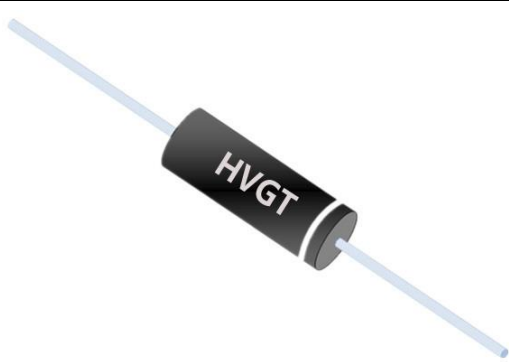
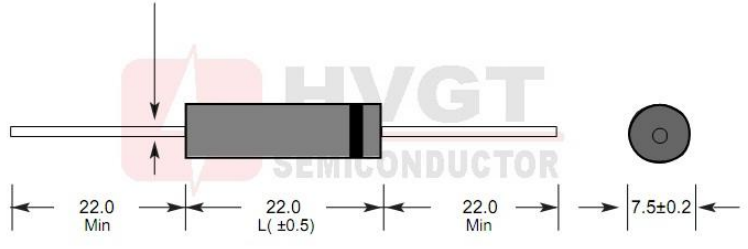


<p>INTRODUCE: HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.</p> <p>FEATURES:</p> <ol style="list-style-type: none"> 1. High overload surge capability. 2. High Current,Low Forward Voltage. 3. Avalanche Characteristic. 4. Conform to RoHS and SGS. 5. Epoxy resin molded in vacuumHave anticorrosion in the surface. <p>APPLICATIONS:</p> <ol style="list-style-type: none"> 1. High voltage power supply rectifier. 2. High voltage rectifier circuit for microwave oven. 3. Other. <p>MECHANICAL DATA:</p> <ol style="list-style-type: none"> 1. Case: epoxy resin molding. 2. Terminal: welding axis. 3. Net weight: 2.50 grams (approx). 	<p>SHAPE DISPLAY:</p> 	<p>Part Marking:</p> <p>Code:</p> <p style="text-align: center;">T3509H HVGT</p> <p>Cathode Mark:</p> <p style="text-align: center;"> </p>
	<p>SIZE: (Unit:mm)</p>	<p>HVGT NAME: DO-722</p>
	<p>DO-722 Series Lead Diameter 1.2mm ±0.02</p>  <p style="text-align: center;">Unit:mm</p>	

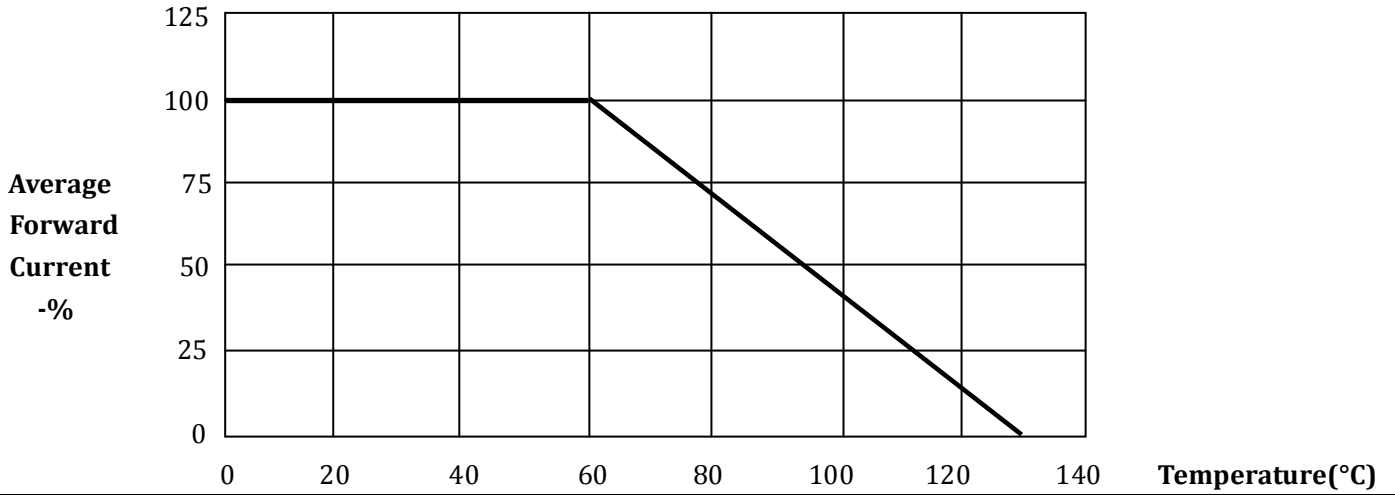
MAXIMUM RATINGS AND CHARACTERISTICS: Ta=25°C (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}		9.0	kV
Average Forward Current Maximum	I _{FAVM}	60Hz Half-Sine Wave, Resistance Load, Ta=60°C	350	mA
Non-Repetitive Forward Surge Current	I _{FSM}	60Hz Half-Sine Wave; 8.3ms; 1Cycle	30	A
Reverse surge current	I _{RSM}	Wp=1ms, Rectangular-Wave, One-shot,	100	mA
Junction Temperature	T _J		130	°C
Allowable Operation Case Temperature	T _C		-40~+130	°C
Storage Temperature	T _{STG}		-40~+130	°C

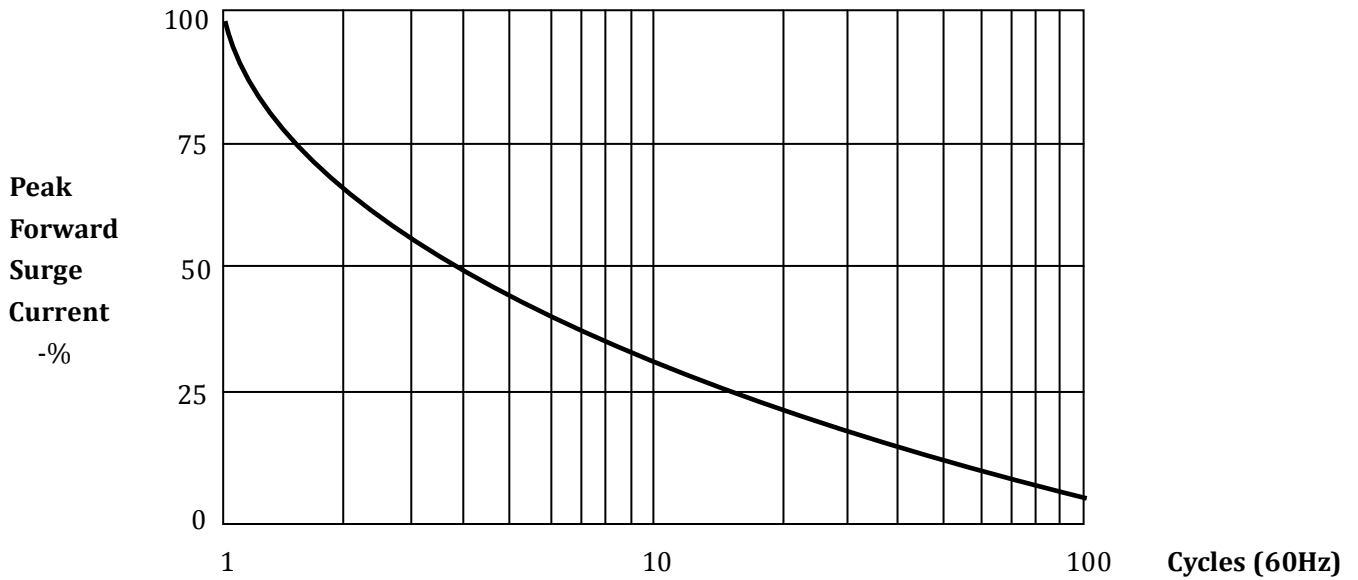
ELECTRICAL CHARACTERISTICS: Ta=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V _{FM}	at 25°C; at I _{FAVM}	10	V
Maximum Reverse Current	I _{R1}	at 25°C; at V _{RRM}	5.0	uA
	I _{R2}	at 100°C; at V _{RRM}	50	uA
Maximum Reverse Recovery Time	T _{RR}	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	--	nS
Reverse Breakdown Voltage	V _Z	at 25°C; I _R =100uA	9.5	kV

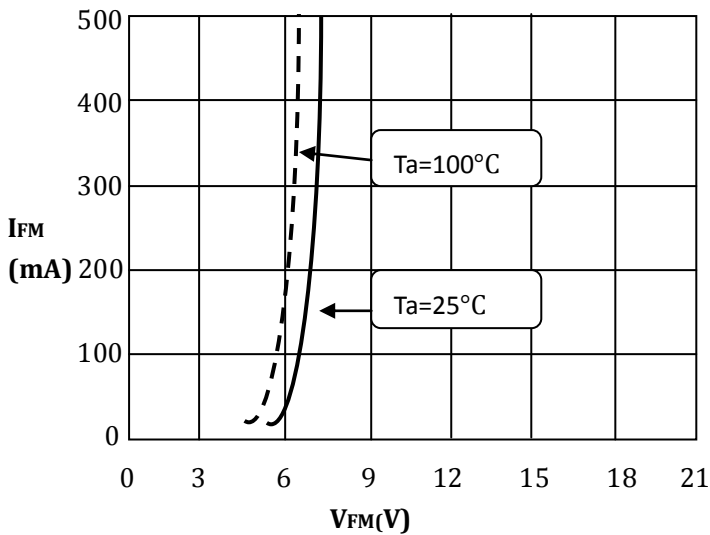
Forward Current Derating Curves



Non-Repetitive Surge Current



Forward Characteristics



Reverse Characteristics

